

# Silizium-PIN-Fotodiode mit Tageslichtsperrfilter Silicon PIN Photodiode with Daylight Filter

## SFH 235 FA



### Wesentliche Merkmale

- Speziell geeignet für Anwendungen bei 880 nm
- Kurze Schaltzeit (typ. 20 ns)
- 5 mm-Plastikbauform im LED-Gehäuse
- Auch gegurtet lieferbar

### Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern und Gerätefernsteuerungen
- Lichtschranken für Gleich- und Wechsellichtbetrieb

### Features

- Especially suitable for applications of 880 nm
- Short switching time (typ. 20 ns)
- 5 mm LED plastic package
- Also available on tape and reel

### Applications

- IR-remote control of hi-fi and TV sets, video tape recorders, dimmers, remote control of various equipment
- Photointerrupters

| Typ<br>Type | Bestellnummer<br>Ordering Code |
|-------------|--------------------------------|
| SFH 235 FA  | Q62702-P273                    |

**Grenzwerte**  
**Maximum Ratings**

| Bezeichnung<br>Parameter                                                                                                                                      | Symbol<br>Symbol  | Wert<br>Value | Einheit<br>Unit |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------|---------------|-----------------|
| Betriebs- und Lagertemperatur<br>Operating and storage temperature range                                                                                      | $T_{op}; T_{stg}$ | - 40 ... + 80 | °C              |
| Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt<br>bei Lötzeit $t \leq 3$ s)<br>Soldering temperature in 2 mm distance from case<br>bottom ( $t \leq 3$ s) | $T_S$             | 230           | °C              |
| Sperrspannung<br>Reverse voltage                                                                                                                              | $V_R$             | 32            | V               |
| Verlustleistung, $T_A = 25$ °C<br>Total power dissipation                                                                                                     | $P_{tot}$         | 150           | mW              |

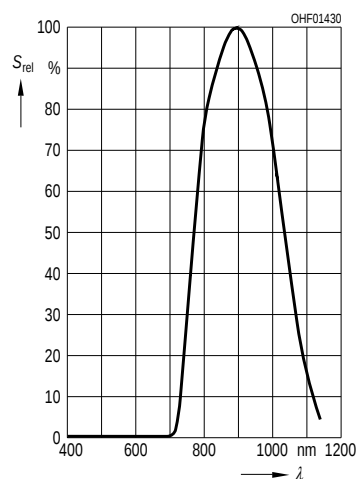
**Kennwerte** ( $T_A = 25$  °C,  $\lambda = 870$  nm)  
**Characteristics**

| Bezeichnung<br>Parameter                                                                                                           | Symbol<br>Symbol             | Wert<br>Value      | Einheit<br>Unit |
|------------------------------------------------------------------------------------------------------------------------------------|------------------------------|--------------------|-----------------|
| Fotostrom<br>Photocurrent<br>$V_R = 5$ V, $E_e = 1$ mW/cm <sup>2</sup>                                                             | $I_P$                        | 50 ( $\geq 40$ )   | µA              |
| Wellenlänge der max. Fotoempfindlichkeit<br>Wavelength of max. sensitivity                                                         | $\lambda_{S\ max}$           | 900                | nm              |
| Spektraler Bereich der Fotoempfindlichkeit<br>$S = 10\%$ von $S_{max}$<br>Spectral range of sensitivity<br>$S = 10\%$ of $S_{max}$ | $\lambda$                    | 740 ... 1120       | nm              |
| Bestrahlungsempfindliche Fläche<br>Radiant sensitive area                                                                          | $A$                          | 7                  | mm <sup>2</sup> |
| Abmessung der bestrahlungsempfindlichen Fläche<br>Dimensions of radiant sensitive area                                             | $L \times B$<br>$L \times W$ | $2.65 \times 2.65$ | mm × mm         |
| Abstand Chipoberfläche zu Gehäuseoberfläche<br>Distance chip front to case surface                                                 | $H$                          | 0.6 ... 0.8        | mm              |
| Halbwinkel<br>Half angle                                                                                                           | $\varphi$                    | $\pm 65$           | Grad<br>deg.    |
| Dunkelstrom, $V_R = 10$ V<br>Dark current                                                                                          | $I_R$                        | 2 ( $\leq 30$ )    | nA              |

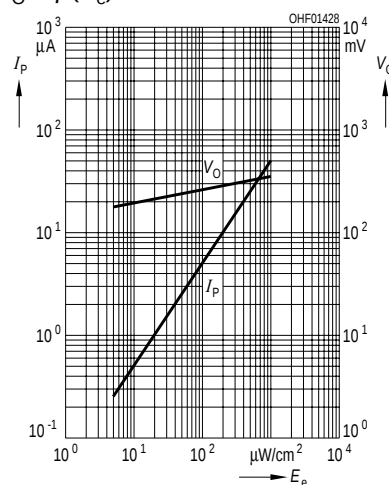
**Kennwerte** ( $T_A = 25\text{ °C}$ ,  $\lambda = 870\text{ nm}$ )  
**Characteristics** (cont'd)

| Bezeichnung<br>Parameter                                                                                                                                                             | Symbol<br>Symbol | Wert<br>Value         | Einheit<br>Unit                                      |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------|-----------------------|------------------------------------------------------|
| Spektrale Fotoempfindlichkeit<br>Spectral sensitivity                                                                                                                                | $S_\lambda$      | 0.63                  | A/W                                                  |
| Quantenausbeute<br>Quantum yield                                                                                                                                                     | $\eta$           | 0.9                   | <u>Electrons</u><br>Photon                           |
| Leerlaufspannung, $E_e = 0.5\text{ mW/cm}^2$<br>Open-circuit voltage                                                                                                                 | $V_O$            | 320 ( $\geq 250$ )    | mV                                                   |
| Kurzschlußstrom, $E_e = 0.5\text{ mW/cm}^2$<br>Short-circuit current                                                                                                                 | $I_{SC}$         | 22                    | $\mu\text{A}$                                        |
| Anstiegs- und Abfallzeit des Fotostromes<br>Rise and fall time of the photocurrent<br>$R_L = 50\ \Omega$ ; $V_R = 5\text{ V}$ ; $\lambda = 850\text{ nm}$ ; $I_p = 800\ \mu\text{A}$ | $t_r, t_f$       | 20                    | ns                                                   |
| Durchlaßspannung, $I_F = 100\text{ mA}$ , $E = 0$<br>Forward voltage                                                                                                                 | $V_F$            | 1.3                   | V                                                    |
| Kapazität, $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$<br>Capacitance                                                                                                          | $C_0$            | 72                    | pF                                                   |
| Temperaturkoeffizient von $V_O$<br>Temperature coefficient of $V_O$                                                                                                                  | $TC_V$           | - 2.6                 | mV/K                                                 |
| Temperaturkoeffizient von $I_{SC}$<br>Temperature coefficient of $I_{SC}$                                                                                                            | $TC_I$           | 0.03                  | %/K                                                  |
| Rauschäquivalente Strahlungsleistung<br>Noise equivalent power<br>$V_R = 10\text{ V}$                                                                                                | $NEP$            | $4.0 \times 10^{-14}$ | $\frac{\text{W}}{\sqrt{\text{Hz}}}$                  |
| Nachweisgrenze, $V_R = 10\text{ V}$<br>Detection limit                                                                                                                               | $D^*$            | $6.6 \times 10^{12}$  | $\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$ |

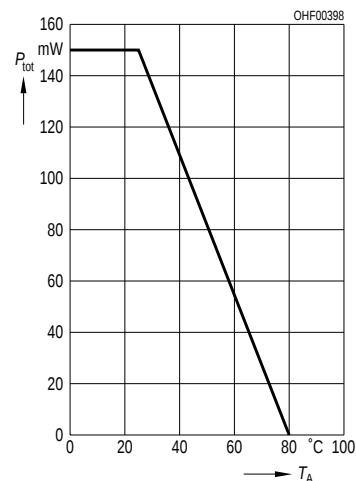
### Relative Spectral Sensitivity

$$S_{\text{rel}} = f(\lambda)$$


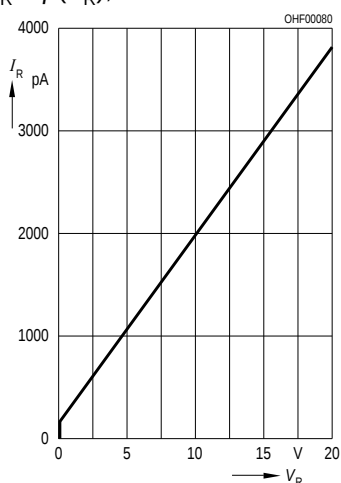
### Photocurrent $I_P = f(E_e)$ , $V_R = 5 \text{ V}$ Open-Circuit Voltage $V_O = f(E_e)$



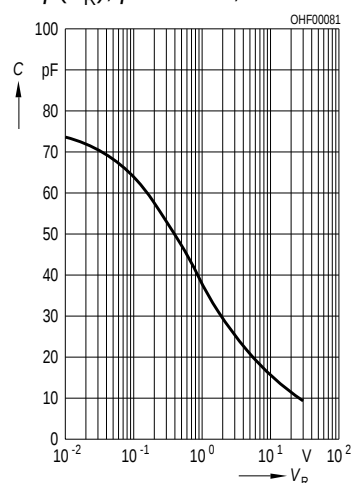
### Total Power Dissipation

$$P_{\text{tot}} = f(T_A)$$


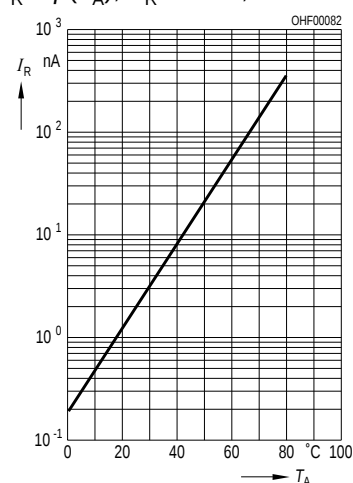
### Dark Current

$$I_R = f(V_R), E = 0$$


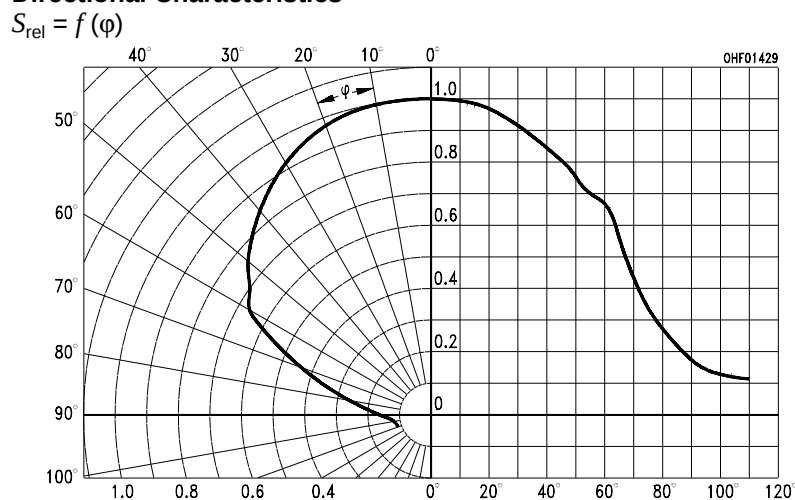
### Capacitance

$$C = f(V_R), f = 1 \text{ MHz}, E = 0$$


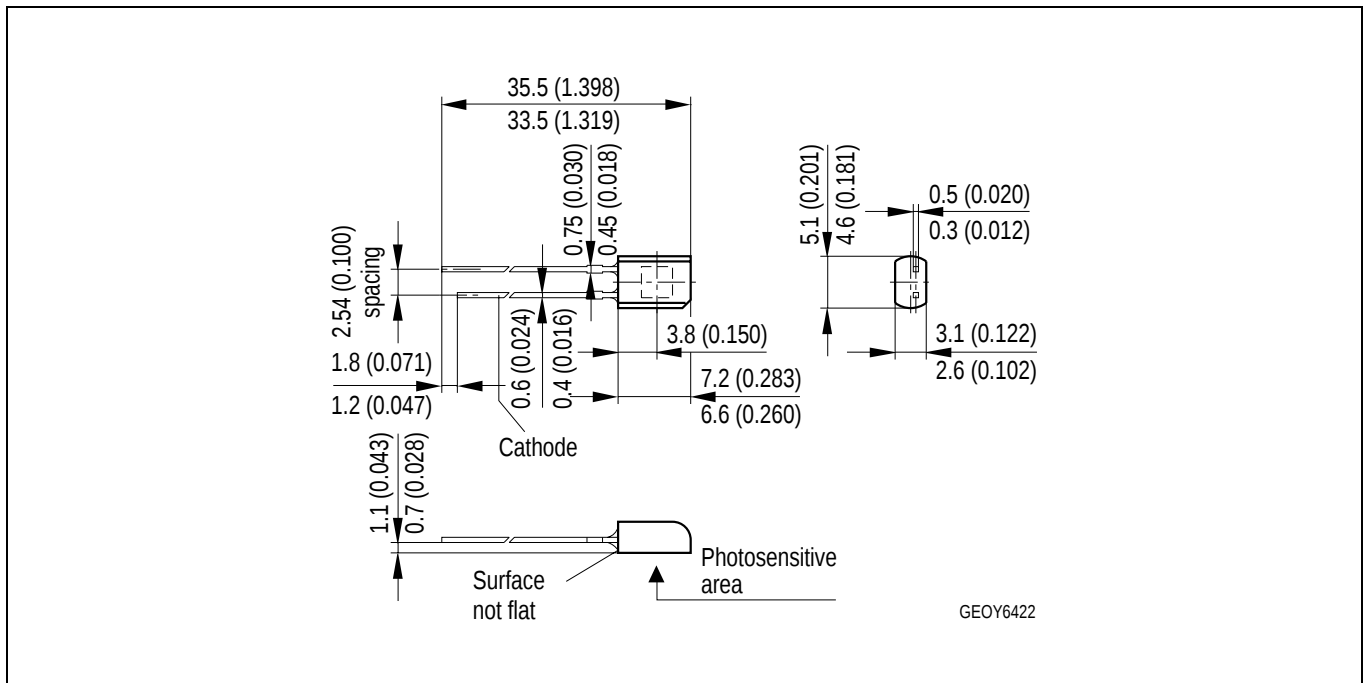
### Dark Current

$$I_R = f(T_A), V_R = 10 \text{ V}, E = 0$$


### Directional Characteristics

$$S_{\text{rel}} = f(\varphi)$$


## Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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### Attention please!

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### Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

**Components used in life-support devices or systems must be expressly authorized for such purpose!** Critical components <sup>1</sup>, may only be used in life-support devices or systems <sup>2</sup> with the express written approval of OSRAM OS.

<sup>1</sup> A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

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